

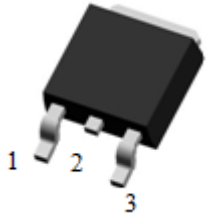
N-Channel Logic Level Enhancement Mode Field Effect Transistor (40V, 18A)

PRODUCT SUMMARY		
V _{DSS}	I _D	R _{DS(on)} (mΩ) Max
40V	18A	25 @ V _{GS} = 10V, I _D = 12A
		45 @ V _{GS} = 4.5V, I _D = 10A

Features

- Rugged and reliable
- Surface Mount package
- High power and current handing capability
- Super high dense cell design for extremely low R_{DS(on)}
- Ordering information : GD2504-G(Lead(Pb)-free and halogen-free)

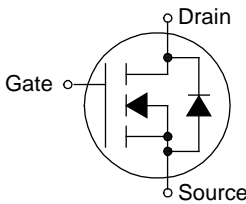




GD2504-G Pin Assignment & Symbol

3-Lead Plastic **TO-252**

Pin 1: Gate Pin 2: Source Pin 3: Drain



Absolute Maximum Ratings (T_A=25°C, unless otherwise noted)

Symbol	Parameter	Ratings	Units
V _{DS}	Drain-Source Voltage	40	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current @T _c =25°C	18	A
I _{DM}	Drain Current (Pulsed) ^a	45	A
P _D	Total Power Dissipation @T _A =25°C	6	W
I _{AS} ^c	Avalanche Current, Single Pulse @L=0.3mH	8.6	A
E _{AS} ^c	Avalanche energy, Single Pulse @L=0.3mH	11	mJ
T _{stg}	Storage Temperature Range	-55 to +150	°C
T _j	Junction Temperature	150	°C
R _{θJA}	Thermal Resistance Junction to Ambient (PCB mounted) ^b	50	°C/W

Note: a: Repetitive Rating; Pulse width limited by the maximum junction temperature

b: 1-in² 2oz Cu PCB board

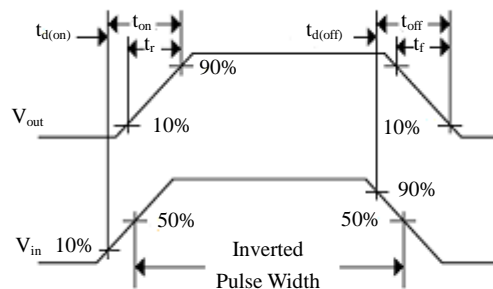
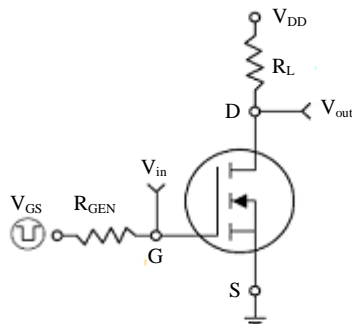
c: Repetitive rating, pulse width limited by junction temperature T_j =25°C

Electrical Characteristics (T_A=25 °C, unless otherwise noted)

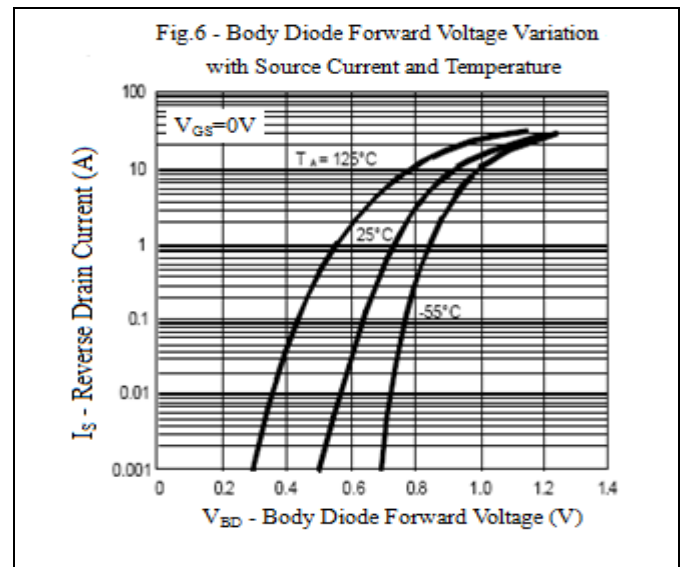
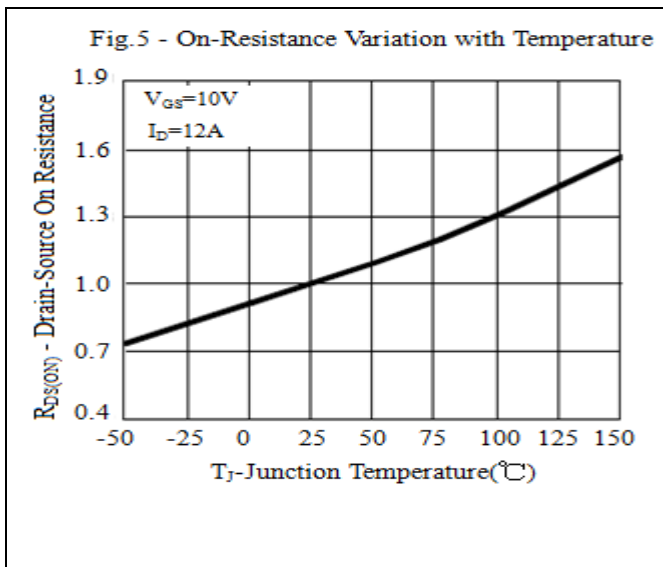
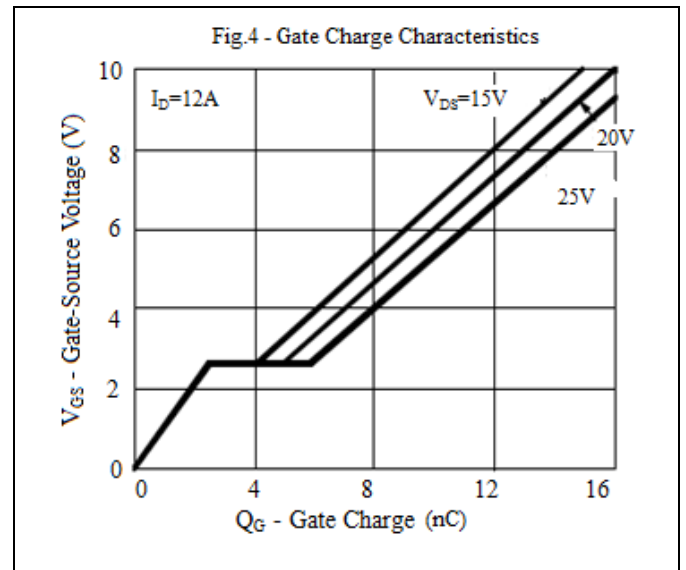
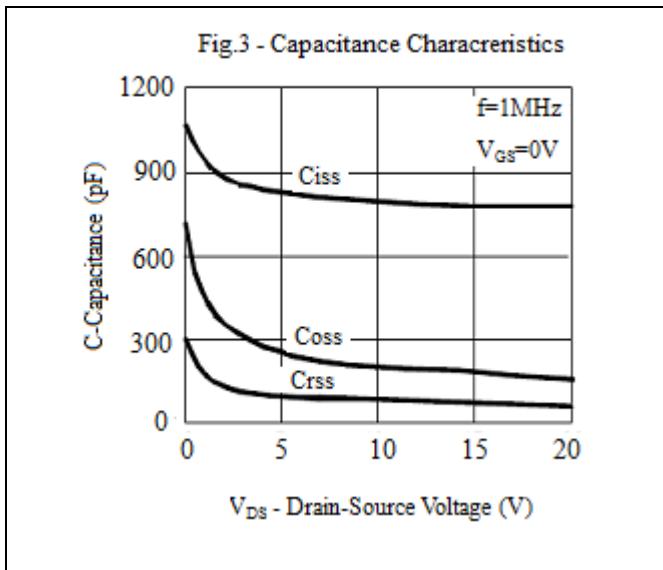
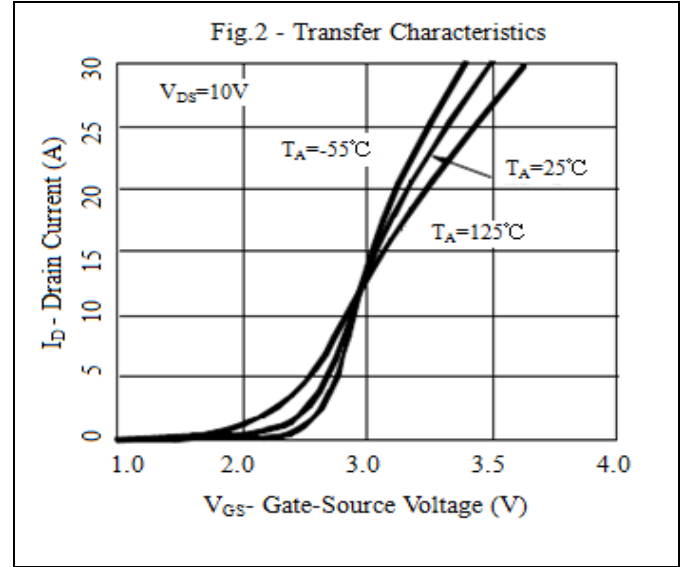
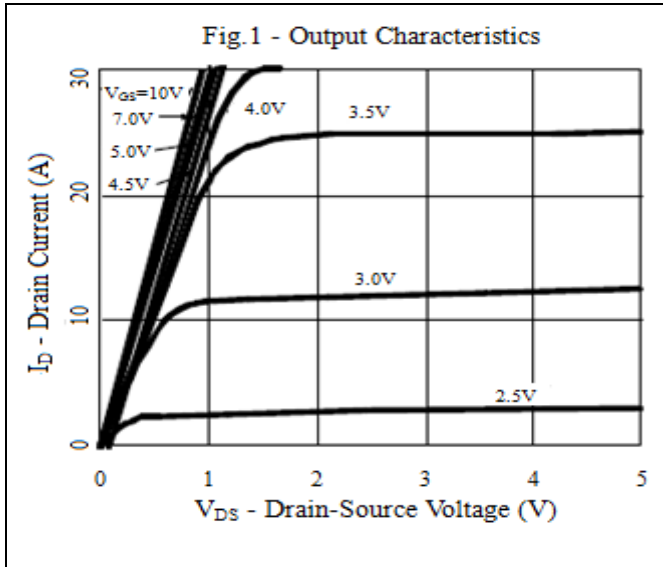
Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
• Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =32V, V _{GS} =0V	-	-	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±250	nA
• On Characteristics ^d						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	-	3.0	V
I _{DS(on)}	On-State Drain Current	V _{DS} =10V, V _{GS} =10V	45	-	-	A
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D = 12A	-	18	25	mΩ
		V _{GS} =4.5V, I _D = 10A	-	26	45	
g _{FS}	Forward Transconductance	V _{DS} =10V, I _D = 12A	-	18	-	S
• Dynamic Characteristics ^e						
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	-	760	-	pF
C _{oss}	Output Capacitance		-	165	-	
C _{rss}	Reverse Transfer Capacitance		-	55	-	
• Switching Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =20V, I _D =12A, V _{GS} =10V	-	16	-	nC
Q _{gs}	Gate-Source Charge		-	2.5	-	
Q _{gd}	Gate-Drain Charge		-	2.1	-	
t _{d(on)}	Turn-on Delay Time	V _{DD} = 20V, R _L =1Ω, I _D =1A, V _{GS} =10V, R _{GEN} =6Ω	-	2.1	4.2	nS
t _r	Turn-on Rise Time		-	7.2	14	
t _{d(off)}	Turn-off Delay Time		-	11.6	21	
t _f	Turn-off Fall Time		-	3.5	7.2	
• Drain-Source Diode Characteristics						
I _S	Continuous Current		-	-	12	A
I _{SM}	Pulsed Current		-	-	40	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} =0V, I _F = I _S	-	-	1.2	V

Note: d: Pulse Test : Pulse Width < 300μs, Duty Cycle < 2%

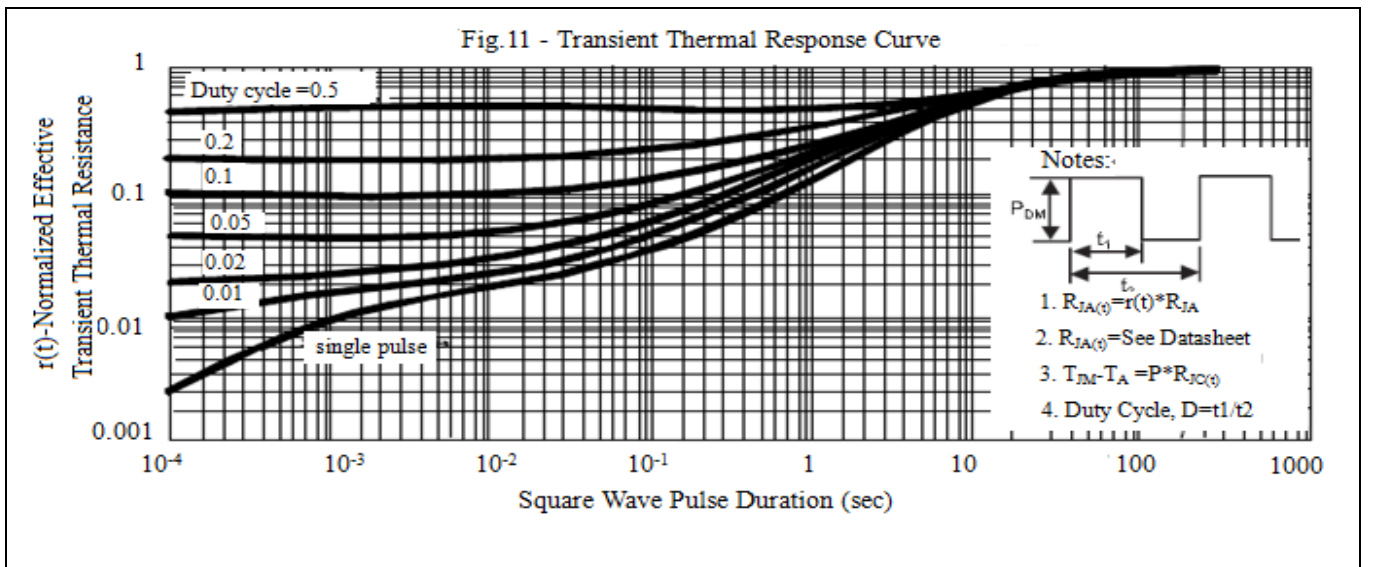
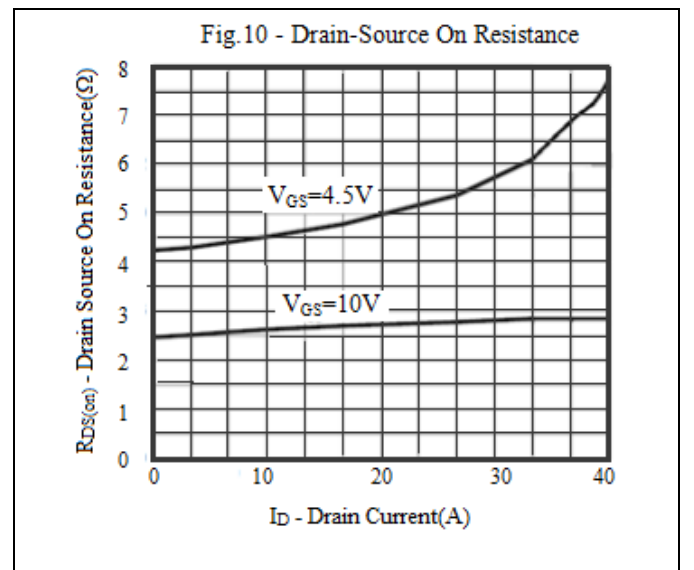
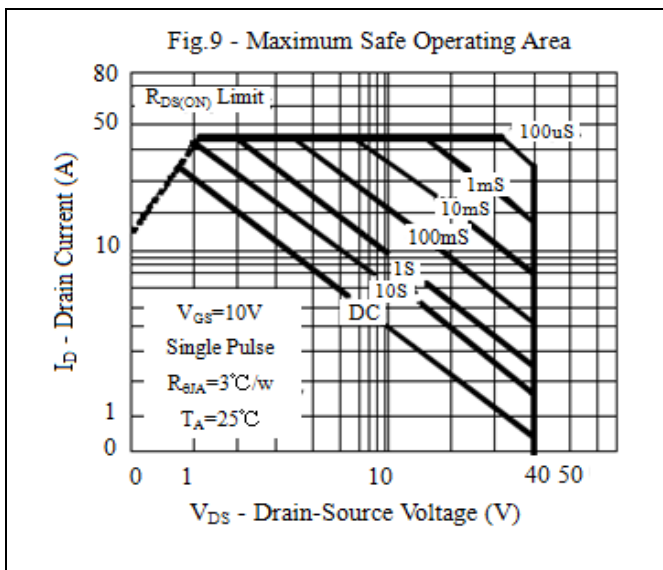
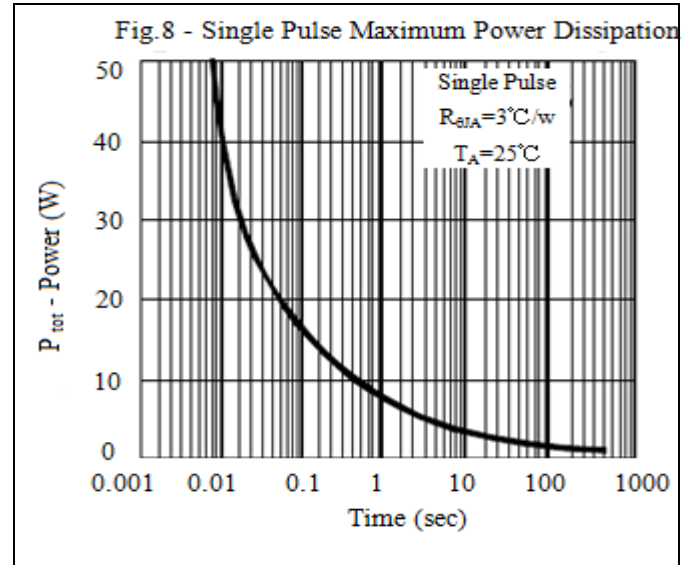
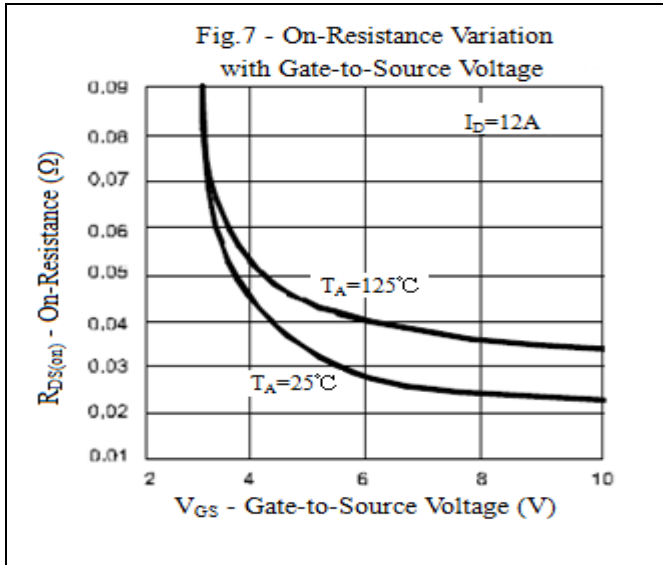
e: Guaranteed by design, not subject to production testing



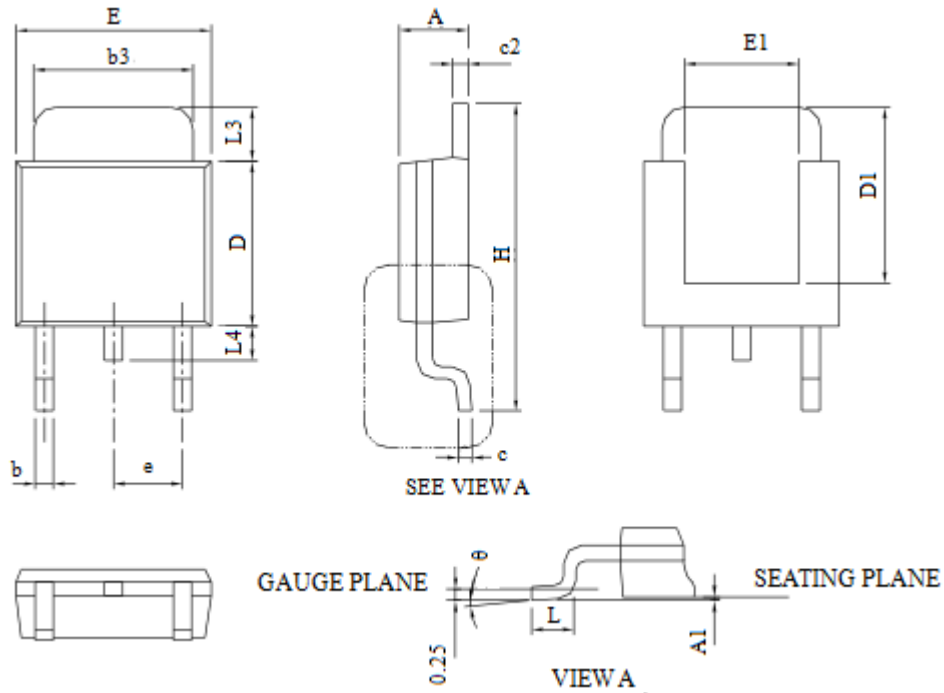
Characteristics Curve



Characteristics Curve



TO-252 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters(MM)		Dimensions In Inches(MIL)	
	Min	Max	Min	Max
A	2.180	2.390	0.086	0.094
A1	0.000	0.130	0.000	0.005
b	0.500	0.890	0.020	0.035
b3	4.950	5.460	0.195	0.215
c	0.460	0.610	0.018	0.024
c2	0.460	0.890	0.018	0.035
D	5.330	6.220	0.21	0.245
D1	4.570	6.000	0.180	0.236
E	6.350	6.730	0.250	0.265
E1	3.810	6.000	0.150	0.236
e	2.290BSC		0.090BSC	
H	9.400	10.41	0.370	0.410
L	0.900	1.780	0.0035	0.070
L3	0.890	2.030	0.035	0.080
L4	0000	1.020	0000	0.040
ø	0 ⁰	8 ⁰	0 ⁰	8 ⁰



Notice

1. Specification of the products displayed herein is subject to change without notice. Continuous development may necessitate changes in technical data without notice. GEMMICRO or anyone on its behalf assumes no responsibility or liability for any errors or inaccuracies.
2. Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.